

TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type (U-MOS V-H)

TPC8034-H

High-Efficiency DC/DC Converter Applications
 Notebook PC Applications
 Portable Equipment Applications

- Small footprint due to a small and thin package
- High-speed switching
- Small gate charge: $Q_{SW} = 16 \text{ nC}$ (typ.)
- Low drain-source ON-resistance: $R_{DS(ON)} = 2.6 \text{ m}\Omega$ (typ.)
- High forward transfer admittance: $|Y_{fs}| = 67 \text{ S}$ (typ.)
- Low leakage current: $I_{DSS} = 10 \text{ }\mu\text{A}$ (max) ($V_{DS} = 30 \text{ V}$)
- Enhancement mode: $V_{th} = 1.5 \text{ to } 2.5 \text{ V}$ ($V_{DS} = 10 \text{ V}$, $I_D = 1 \text{ mA}$)

Absolute Maximum Ratings (Ta = 25°C)

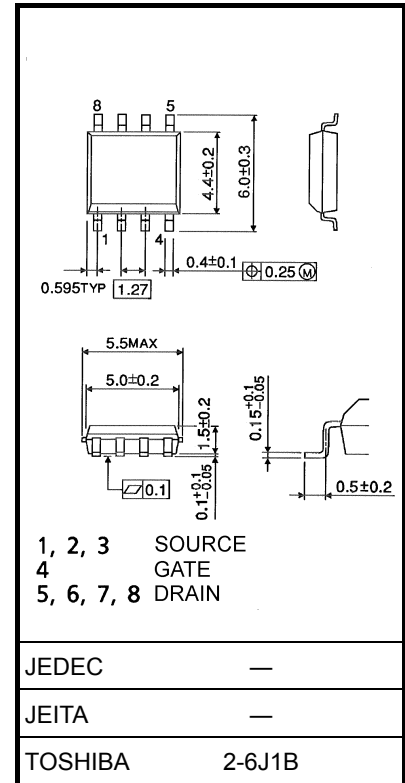
Characteristic		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	30	V
Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$)		V_{DGR}	30	V
Gate-source voltage		V_{GSS}	± 20	V
Drain current	DC (Note 1)	I_D	18	A
	Pulsed (Note 1)	I_{DP}	72	
Drain power dissipation (t = 10 s) (Note 2a)		P_D	1.9	W
Drain power dissipation (t = 10 s) (Note 2b)		P_D	1.0	W
Single-pulse avalanche energy (Note 3)		E_{AS}	211	mJ
Avalanche current		I_{AR}	18	A
Repetitive avalanche energy (Note 2a) (Note 4)		E_{AR}	0.082	mJ
Channel temperature		T_{ch}	150	°C
Storage temperature range		T_{stg}	-55 to 150	°C

Note 1, Note 2, Note 3 and Note 4: See the next page.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

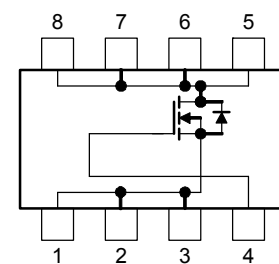
This transistor is an electrostatic-sensitive device. Handle with care.

Unit: mm



Weight: 0.085 g (typ.)

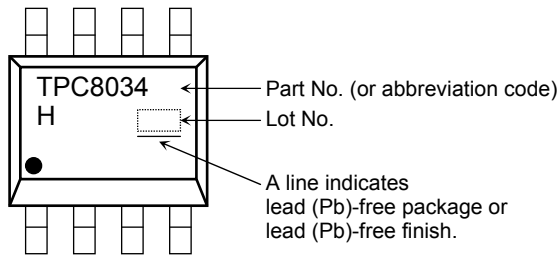
Circuit Configuration



Thermal Characteristics

Characteristic	Symbol	Max	Unit
Thermal resistance, channel to ambient (t = 10 s) (Note 2a)	$R_{th(ch-a)}$	65.8	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	$R_{th(ch-a)}$	125	°C/W

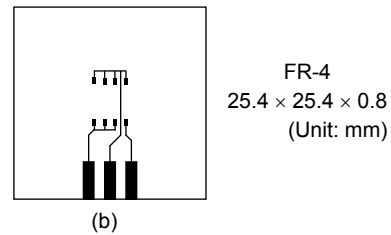
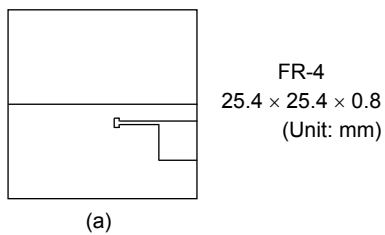
Marking (Note 5)



Note 1: The channel temperature should not exceed 150°C during use.

Note 2: (a) Device mounted on a glass-epoxy board (a)

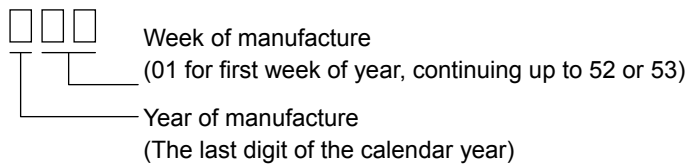
(b) Device mounted on a glass-epoxy board (b)



Note 3: $V_{DD} = 24\text{ V}$, $T_{ch} = 25^\circ\text{C}$ (initial), $L = 500\ \mu\text{H}$, $R_G = 25\ \Omega$, $I_{AR} = 18\ \text{A}$

Note 4: Repetitive rating: pulse width limited by max channel temperature

Note 5: * Weekly code: (Three digits)

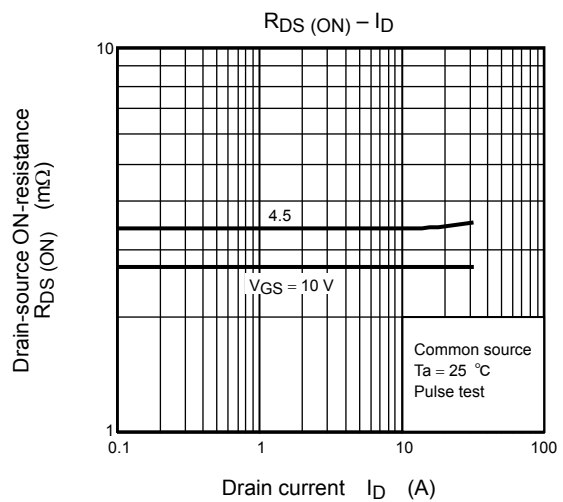
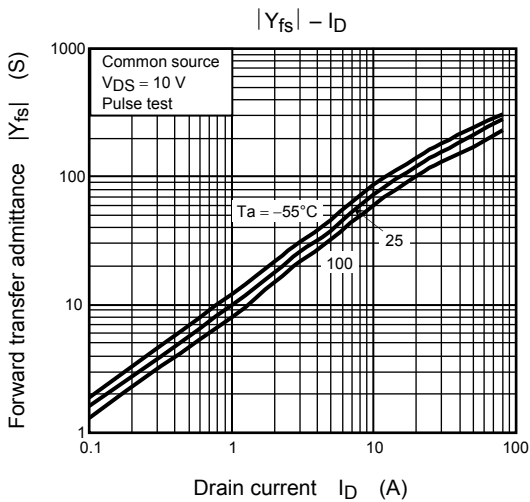
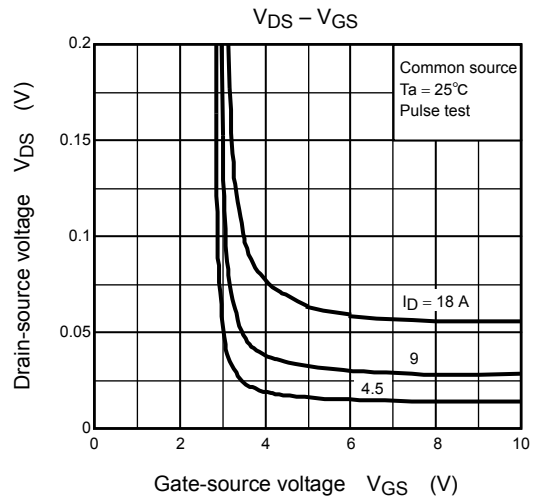
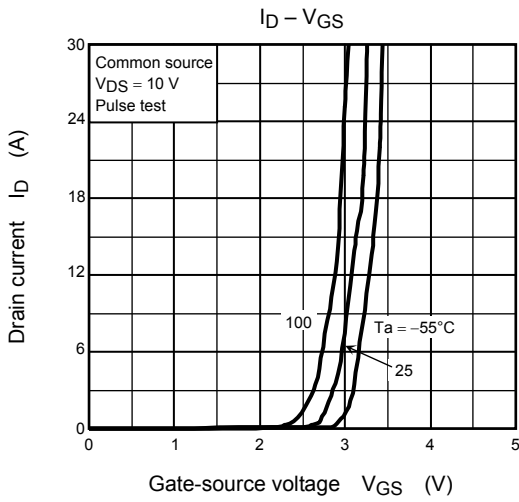
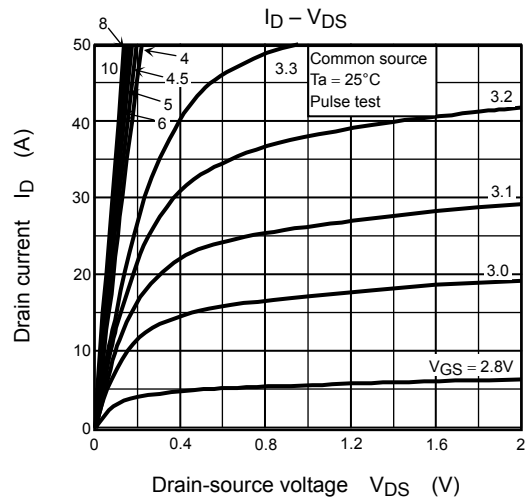
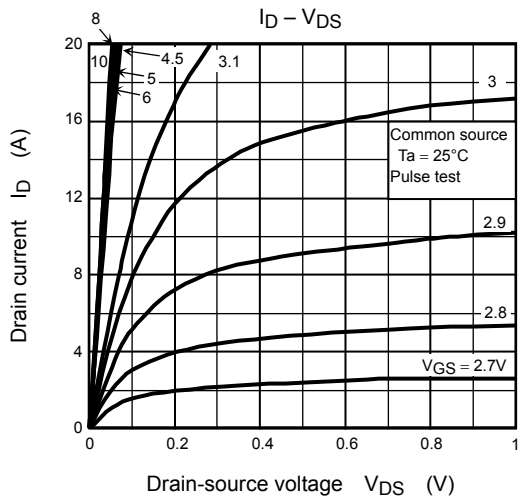


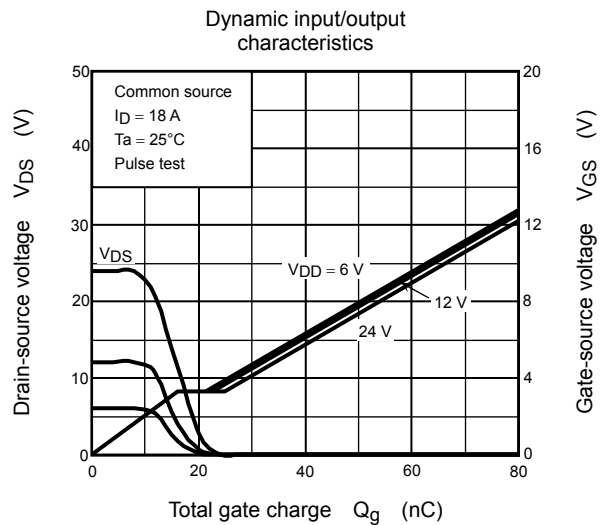
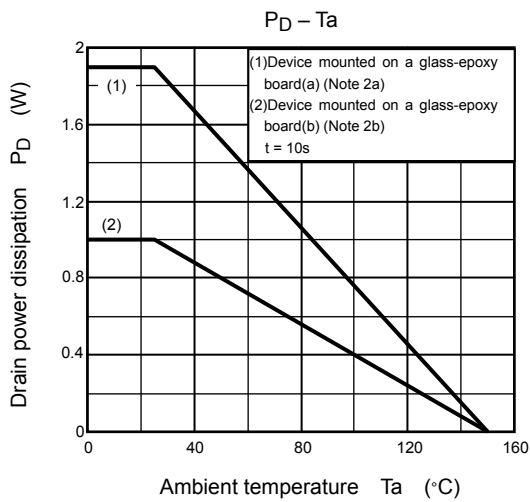
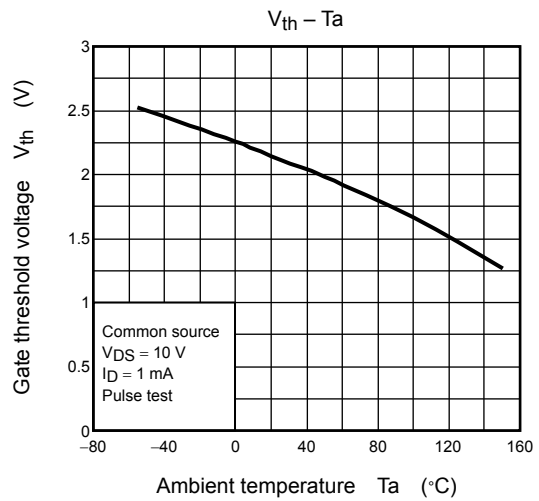
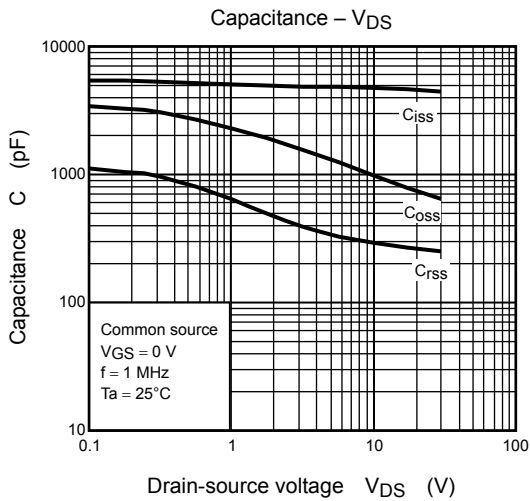
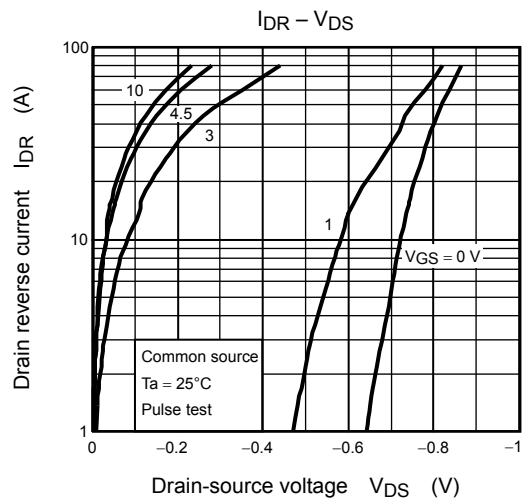
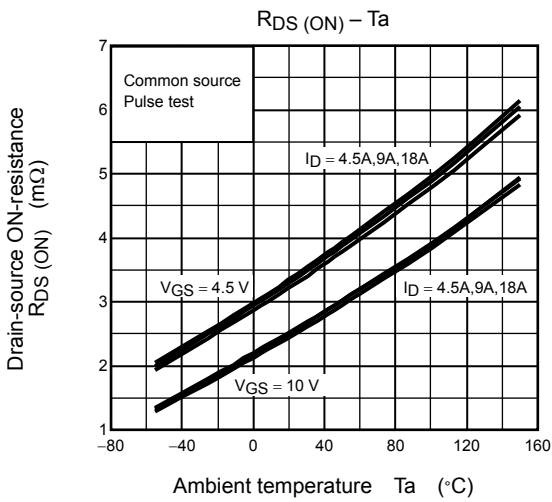
Electrical Characteristics (Ta = 25°C)

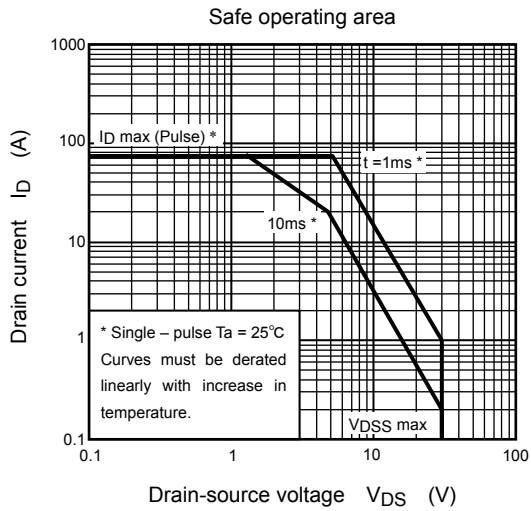
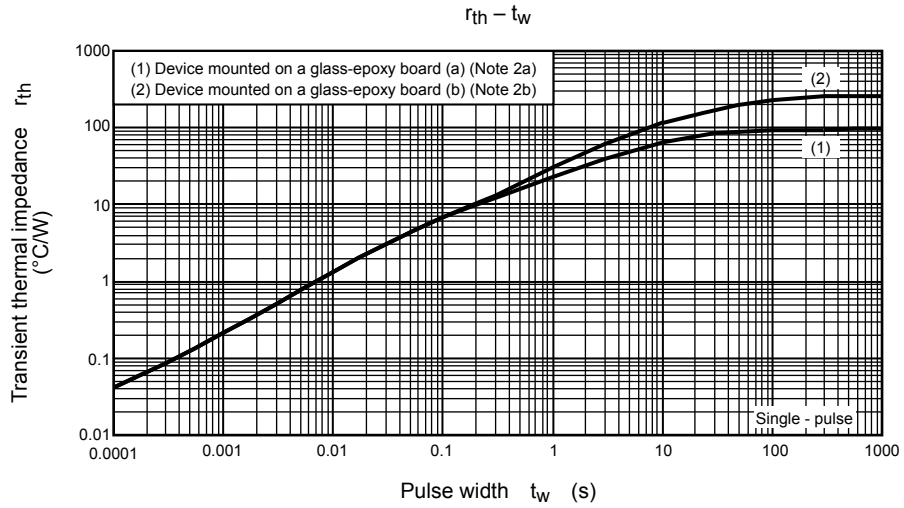
Characteristic		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GSS}	$V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$	—	—	± 100	nA
Drain cutoff current		I_{DSS}	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$	—	—	10	μA
Drain-source breakdown voltage		$V_{(BR)DSS}$	$I_D = 10\text{ mA}, V_{GS} = 0\text{ V}$	30	—	—	V
		$V_{(BR)DSX}$	$I_D = 10\text{ mA}, V_{GS} = -20\text{ V}$	15	—	—	
Gate threshold voltage		V_{th}	$V_{DS} = 10\text{ V}, I_D = 1\text{ mA}$	1.5	—	2.5	V
Drain-source ON-resistance		$R_{DS(ON)}$	$V_{GS} = 4.5\text{ V}, I_D = 9\text{ A}$	—	3.4	4.5	m Ω
			$V_{GS} = 10\text{ V}, I_D = 9\text{ A}$	—	2.6	3.5	
Forward transfer admittance		$ Y_{fs} $	$V_{DS} = 10\text{ V}, I_D = 9\text{ A}$	32.5	65	—	S
Input capacitance		C_{iss}	$V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	—	4614	6150	pF
Reverse transfer capacitance		C_{rss}		—	284	426	
Output capacitance		C_{oss}		—	1100	—	
Gate resistance		R_g	$V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V}, f = 5\text{ MHz}$	—	1.0	1.5	Ω
Switching time	Rise time	t_r	<p>$V_{GS} = 10\text{ V}, 0\text{ V}$ $I_D = 9\text{ A}$ V_{OUT} 4.7 nF $R_L = 1.5\Omega$ $V_{DD} \approx 15\text{ V}$ Duty $\leq 1\%$, $t_w = 10\text{ }\mu\text{s}$</p>	—	6.0	—	ns
	Turn-on time	t_{on}		—	18	—	
	Fall time	t_f		—	8.8	—	
	Turn-off time	t_{off}		—	59	—	
Total gate charge (gate-source plus gate-drain)		Q_g	$V_{DD} \approx 24\text{ V}, V_{GS} = 10\text{ V}, I_D = 18\text{ A}$	—	68	—	nC
			$V_{DD} \approx 24\text{ V}, V_{GS} = 5\text{ V}, I_D = 18\text{ A}$	—	35	—	
Gate-source charge 1		Q_{gs1}	$V_{DD} \approx 24\text{ V}, V_{GS} = 10\text{ V}, I_D = 18\text{ A}$	—	16	—	
Gate-drain ("Miller") charge		Q_{gd}	$V_{DD} \approx 24\text{ V}, V_{GS} = 10\text{ V}, I_D = 18\text{ A}$	—	9	—	
Gate switch charge		Q_{sw}	$V_{DD} \approx 24\text{ V}, V_{GS} = 10\text{ V}, I_D = 18\text{ A}$	—	16	—	

Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Drain reverse current	Pulse (Note 1)	I_{DRP}	—	—	—	72	A
Forward voltage (diode)		V_{DSF}	$I_{DR} = 18\text{ A}, V_{GS} = 0\text{ V}$	—	—	-1.2	V







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